

ABSTRACT

WAFER THINNING METHOD

Disclosed herein is a wafer thinning method for thinning a wafer formed from an SiC substrate having a first surface and a second surface opposite to the first surface. The wafer thinning method includes an annular groove forming step of forming an annular groove on the second surface of the SiC substrate in an annular area corresponding to the boundary between a device area and a peripheral marginal area in the condition where a thickness corresponding to the finished thickness of the wafer after thinning is left, and a separation start point forming step of applying the laser beam to the second surface as relatively moving a focal point and the SiC substrate to thereby form a modified layer and cracks inside the SiC substrate at the predetermined depth.

(Figure 13)